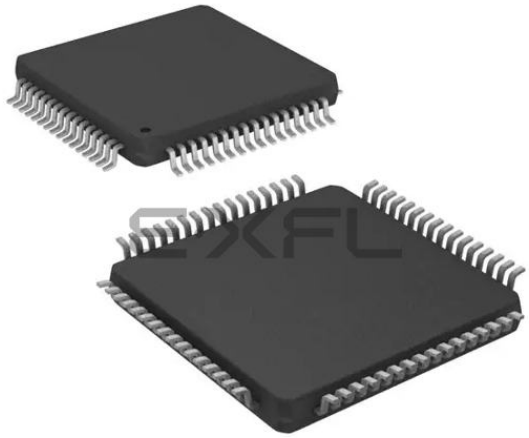

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Number of I/O	51
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Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 23x10/12b; D/A 1x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/sim3l136-c-gq

2. Typical Connection Diagrams

This section provides typical connection diagrams for SiM3L1xx devices.

2.1. Power

Figure 2.1 shows a typical connection diagram for the power pins of the SiM3L1xx devices when the dc-dc buck converter is not used.

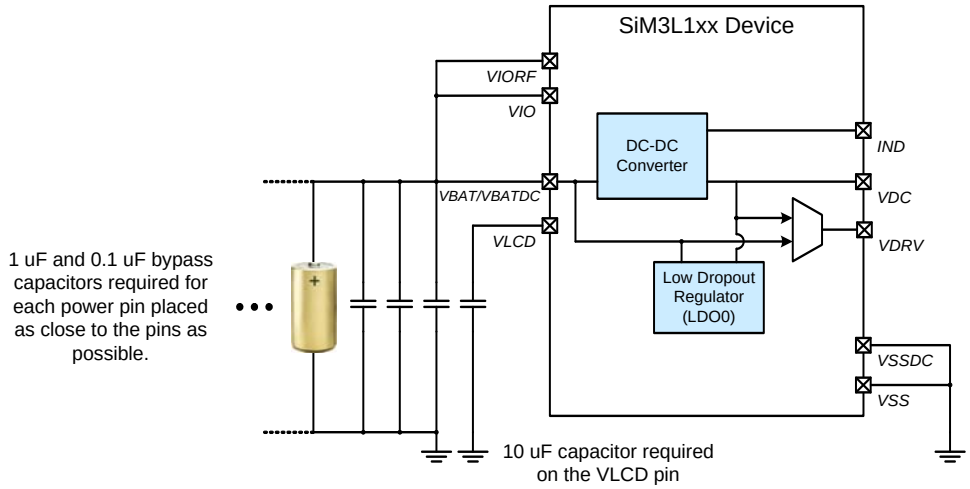

Figure 2.1. Connection Diagram with DC-DC Converter Unused

Figure 2.2 shows a typical connection diagram for the power pins of the SiM3L1xx devices when the internal dc-dc buck converter is in use and I/O are powered directly from the battery.

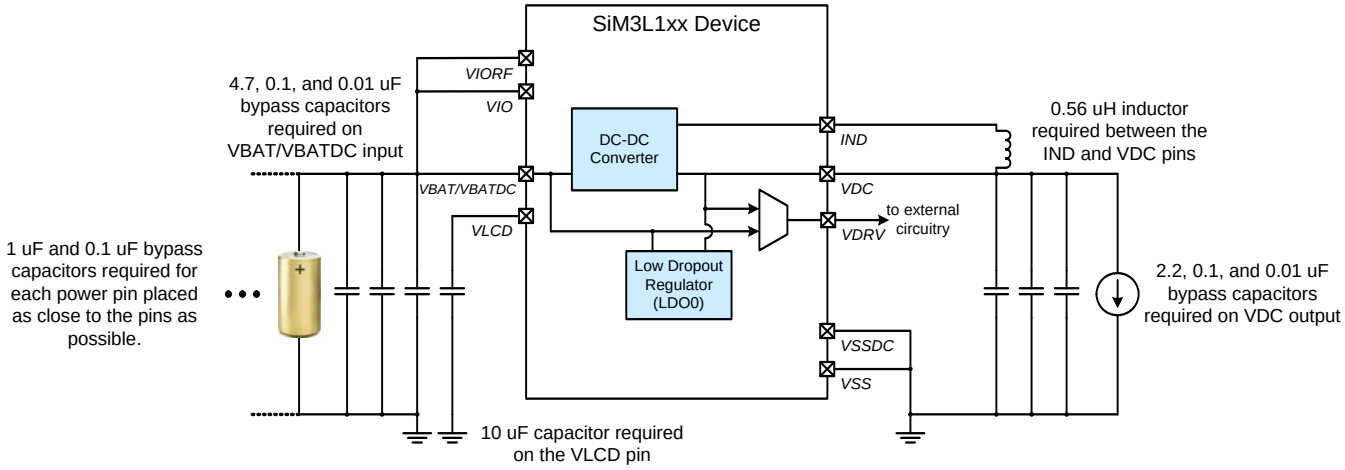

Figure 2.2. Connection Diagram with DC-DC Converter Used and I/O Powered from Battery

Figure 2.3 shows a typical connection diagram for the power pins of the SiM3L1xx devices when used with an external radio device like the Silicon Labs EZRadio® or EZRadioPRO® devices.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 2[1,2,3,4,5]—Core halted with only Port I/O clocks on (wake from pin).	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	4	7.2	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	1.47	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	430	—	µA
Power Mode 3[1,2,6]—Fast-Wake Mode (PM3CLKEN = 1)	I_{BAT}	V_{BAT} = 3.8 V	—	320	530	µA
		V_{BAT} = 1.8 V	—	225	—	µA
Power Mode 4[1,2,4,6]—Slower clock speed with code executing from flash, peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	385	640	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	330	—	µA
Power Mode 5[1,2,4,6]—Slower clock speed with code executing from RAM, peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	320	490	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	275	—	µA
Power Mode 6[1,2,4,6]—Core halted with peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	315	490	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	270	—	µA
Power Mode 8[1,2]—Low Power Sleep, powered through VBAT, VIO, and VIORF at 2.4 V, 32kB of retention RAM	I_{BAT}	RTC Disabled, T_A = 25 °C	—	75	400	nA
		RTC w/ 16.4 kHz LFO, T_A = 25 °C	—	360	—	nA
		RTC w/ 32.768 kHz Crystal, T_A = 25 °C	—	670	—	nA

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.3. Power Mode Wake Up Times

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 2 or 6 Wake Time	t_{PM2}		4	—	5	clocks
Power Mode 3 Fast Wake Time (using LFO as clock source)	t_{PM3FW}		—	425	—	µs
Power Mode 8 Wake Time	t_{PM8}		—	3.8	—	µs

Notes:
1. Wake times are specified as the time from the wake source to the execution phase of the first instruction following WFI. This includes latency to recognize the wake event and fetch the first instruction (assuming wait states = 0).

Table 3.4. Reset and Supply Monitor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
V_{BAT} High Supply Monitor Threshold (VBATHITHEN = 1)	V_{VBATMH}	Early Warning	—	2.20	—	V
		Reset	1.95	2.05	2.1	V
V_{BAT} Low Supply Monitor Threshold (VBATHITHEN = 0)	V_{VBATML}	Early Warning	—	1.85	—	V
		Reset	1.70	1.75	1.77	V
Power-On Reset (POR) Threshold	V_{POR}	Rising Voltage on V_{BAT}	—	1.4	—	V
		Falling Voltage on V_{BAT}	0.8	1	1.3	V
V_{BAT} Ramp Time	t_{RMP}	Time to $V_{BAT} \geq 1.8$ V	10	—	3000	µs
Reset Delay from POR	t_{POR}	Relative to $V_{BAT} \geq V_{POR}$	3	—	100	ms
Reset Delay from non-POR source	t_{RST}	Time between release of reset source and code execution	—	10	—	µs
$\overline{\text{RESET}}$ Low Time to Generate Reset	t_{RSTL}		50	—	—	ns
Missing Clock Detector Response Time (final rising edge to reset)	t_{MCD}	$F_{AHB} > 1$ MHz	—	0.5	1.5	ms
Missing Clock Detector Trigger Frequency	F_{MCD}		—	2.5	10	kHz
V_{BAT} Supply Monitor Turn-On Time	t_{MON}		—	2	—	µs

Table 3.6. Flash Memory

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Write Time[1]	t_{WRITE}	One 16-bit Half Word	20	21	22	µs
Erase Time[1]	t_{ERASE}	One Page	20	21	22	ms
	t_{ERALL}	Full Device	20	21	22	ms
Endurance (Write/Erase Cycles)	N_{WE}		20k	100k	—	Cycles
Retention[2]	t_{RET}	T_A = 25 °C, 1k Cycles	10	100	—	Years

Notes:
1. Does not include sequencing time before and after the write/erase operation, which may take up to 35 µs. During sequential write operations, this extra time is only taken prior to the first write and after the last write.
2. Additional Data Retention Information is published in the Quarterly Quality and Reliability Report.

Table 3.7. Internal Oscillators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Phase-Locked Loop (PLL0OSC)						
Calibrated Output Frequency (Free-running output mode, RANGE = 2)	$f_{PLL0OSC}$	Full Temperature and Supply Range	48.3	49	49.7	MHz
Power Supply Sensitivity (Free-running output mode, RANGE = 2)	$PSS_{PLL0OSC}$	T_A = 25 °C, Fout = 49 MHz	—	300	—	ppm/V
Temperature Sensitivity (Free-running output mode, RANGE = 2)	$TS_{PLL0OSC}$	V_{BAT} = 3.3 V, Fout = 49 MHz	—	50	—	ppm/°C
Adjustable Output Frequency Range	$f_{PLL0OSC}$		23	—	50	MHz
Lock Time	$t_{PLL0LOCK}$	f_{REF} = 20 MHz, $f_{PLL0OSC}$ = 50 MHz M=39, N=99, LOCKTH = 0	—	2.75	—	µs
		f_{REF} = 2.5 MHz, $f_{PLL0OSC}$ = 50 MHz M=19, N=399, LOCKTH = 0	—	9.45	—	µs
		f_{REF} = 32.768 kHz, $f_{PLL0OSC}$ = 50 MHz M=0, N=1524, LOCKTH = 0	—	92	—	µs
Low Power Oscillator (LPOSC0)						
Oscillator Frequency	f_{LPOSC}	Full Temperature and Supply Range	19	20	21	MHz
Divided Oscillator Frequency	f_{LPOSCD}	Full Temperature and Supply Range	2.375	2.5	2.625	MHz
Power Supply Sensitivity	PSS_{LPOSC}	T_A = 25 °C	—	0.5	—	%/V
Temperature Sensitivity	TS_{LPOSC}	V_{BAT} = 3.3 V	—	55	—	ppm/°C
Low Frequency Oscillator (LFOSC0)						
Oscillator Frequency	f_{LFOSC}	Full Temperature and Supply Range	13.4	16.4	19.7	kHz
		T_A = 25 °C, V_{BAT} = 3.3 V	15.8	16.4	17.3	kHz
Power Supply Sensitivity	PSS_{LFOSC}	T_A = 25 °C	—	2.4	—	%/V
Temperature Sensitivity	TS_{LFOSC}	V_{BAT} = 3.3 V	—	0.2	—	%/°C

Table 3.7. Internal Oscillators (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
RTC0 Oscillator (RTC0OSC)						
Missing Clock Detector Trigger Frequency	f_{RTCMCD}		—	8	15	kHz
RTC External Input CMOS Clock Frequency	$f_{RTCEXTCLK}$		0	—	40	kHz
RTC Robust Duty Cycle Range	DC_{RTC}		25	—	55	%

Table 3.8. External Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
External Input CMOS Clock Frequency	f_{CMOS}		0*	—	50	MHz
External Crystal Frequency	f_{XTAL}		0.01	—	25	MHz
External Input CMOS Clock High Time	t_{CMOSH}		9	—	—	ns
External Input CMOS Clock Low Time	t_{CMOSL}		9	—	—	ns
Low Power Mode Charge Pump Supply Range (input from V_{BAT})	V_{BAT}		2.4	—	3.8	V
***Note:** Minimum of 10 kHz when debugging.						

Table 3.11. ACCTR (Advanced Capture Counter) (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
LC Comparator Positive Hysteresis Mode 3 (CPMD = 00)	HYS_{CP+}	CMPHYP = 00	—	1.37	—	mV
		CMPHYP = 01	—	3.8	—	mV
		CMPHYP = 10	—	7.8	—	mV
		CMPHYP = 11	—	15.6	—	mV
LC Comparator Negative Hysteresis Mode 3 (CPMD = 00)	HYS_{CP-}	CMPHYN = 00	—	1.37	—	mV
		CMPHYN = 01	—	–3.9	—	mV
		CMPHYN = 10	—	–7.9	—	mV
		CMPHYN = 11	—	–16	—	mV
LC Comparator Input Range (ACCTR0_LCIN pin)	V_{IN}		–0.25	—	V_{BAT} + 0.25	V
LC Comparator Common-Mode Rejection Ratio	$CMRR_{CP}$		—	75	—	dB
LC Comparator Power Supply Rejection Ratio	$PSRR_{CP}$		—	72	—	dB
LC Comparator Input Offset Voltage	V_{OFF}	T_A = 25 °C	–10	0	10	mV
LC Comparator Input Offset Tempco	TC_{OFF}		—	3.5	—	µV/°C
Reference DAC Offset Error	DAC_{EOFF}		–1	—	1	LSB
Reference DAC Full Scale Output	DAC_{FS}	Low Range	—	V_{IO}/8	—	V
		High Range	—	V_{IO}	—	V
Reference DAC Step Size	DAC_{LSB}	Low Range (48 steps)	—	V_{IO}/384	—	V
		High Range (64 steps)	—	V_{IO}/64	—	V
LC Oscillator Period	T_{LCOSC}		—	25	—	ns
LC Bias Output Impedance	R_{LCBIAS}	10 µA Load	—	1	—	kΩ
LC Bias Drive Strength	I_{LCBIAS}		—	—	2	mA
Pull-Up Resistor Tolerance	R_{TOL}	PUVAL[4:2] = 0 to 6	-15	—	15	%
		PUVAL[4:2] = 7	-10	—	10	%

Table 3.12. Voltage Reference Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Internal Fast Settling Reference						
Output Voltage	V_{REFFS}	–40 to +85 °C, V_{BAT} = 1.8–3.8 V	1.6	1.65	1.7	V
Temperature Coefficient	TC_{REFFS}		—	50	—	ppm/°C
Turn-on Time	t_{REFFS}		—	—	1.5	µs
Power Supply Rejection	$PSRR_{REFFS}$		—	400	—	ppm/V
Internal Precision Reference						
Valid Supply Range	V_{BAT}	VREF2X = 0	1.8	—	3.8	V
		VREF2X = 1	2.7	—	3.8	V
Output Voltage	V_{REFP}	25 °C ambient, VREF2X = 0	1.17	1.2	1.23	V
		25 °C ambient, VREF2X = 1	2.35	2.4	2.45	V
Short-Circuit Current	I_{SC}		—	—	10	mA
Temperature Coefficient	TC_{VREFP}		—	35	—	ppm/°C
Load Regulation	LR_{VREFP}	Load = 0 to 200 µA to VREFGND	—	4.5	—	ppm/µA
Load Capacitor	C_{VREFP}	Load = 0 to 200 µA to VREFGND	0.1	—	—	µF
Turn-on Time	$t_{VREFPON}$	4.7 µF tantalum, 0.1 µF ceramic bypass	—	3.8	—	ms
		0.1 µF ceramic bypass	—	200	—	µs
Power Supply Rejection	$PSRR_{VREFP}$	VREF2X = 0	—	320	—	ppm/V
		VREF2X = 1	—	560	—	ppm/V
External Reference						
Input Current	I_{EXTREF}	Sample Rate = 250 ksps; VREF = 3.0 V	—	5.25	—	µA

Table 3.13. Temperature Sensor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Offset	V_{OFF}	T_A = 0 °C	—	760	—	mV
Offset Error*	E_{OFF}	T_A = 0 °C	—	±14	—	mV
Slope	M		—	2.77	—	mV/°C
Slope Error*	E_M		—	±25	—	µV/°C
Linearity			—	1	—	°C
Turn-on Time			—	1.8	—	µs

***Note:** Absolute input pin voltage is limited by the lower of the supply at VBAT and VIO.

Table 3.14. Comparator (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Positive Hysteresis Mode 3 (CPMD = 11)	HYS_{CP+}	CMPHYP = 00	—	1.37	—	mV
		CMPHYP = 01	—	3.8	—	mV
		CMPHYP = 10	—	7.8	—	mV
		CMPHYP = 11	—	15.6	—	mV
Negative Hysteresis Mode 3 (CPMD = 11)	HYS_{CP-}	CMPHYN = 00	—	1.37	—	mV
		CMPHYN = 01	—	–3.9	—	mV
		CMPHYN = 10	—	–7.9	—	mV
		CMPHYN = 11	—	–16	—	mV
Input Range (CP+ or CP–)	V_{IN}		–0.25	—	V_{BAT} + 0.25	V
Input Pin Capacitance	C_{CP}		—	7.5	—	pF
Common-Mode Rejection Ratio	$CMRR_{CP}$		—	75	—	dB
Power Supply Rejection Ratio	$PSRR_{CP}$		—	72	—	dB
Input Offset Voltage	V_{OFF}	T_A = 25 °C	–10	0	10	mV
Input Offset Tempco	TC_{OFF}		—	3.5	—	µV/°C
Reference DAC Resolution	N_{Bits}			6		bits

Table 3.15. LCD0

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Charge Pump Output Voltage Error	V_{CPERR}		—	±50	—	mV
LCD Clock Frequency	F_{LCD}		16	—	33	kHz

4.1.5.2. Power Mode 1 and Power Mode 5

Power Mode 1 and Power Mode 5 are fully operational modes with code executing from RAM. PM5 is the same as PM1, but with the clocks operating at a lower speed. This enables power to be conserved by reducing the LDO regulator outputs. Compared with the corresponding flash operational mode (Normal or PM4), the active power consumption of the device in these modes is reduced. Additionally, at higher speeds in PM1, the core throughput can also be increased because RAMdoesnot require additional wait states that reduce the instruction fetch speed.

4.1.5.3. Power Mode 2 and Power Mode 6

In Power Mode 2 and Power Mode 6, the core halts and the peripherals continue to run at the selected clock speed. PM6 is the same as PM2, but with the clocks operating at a lower speed. This enables power to be conserved by reducing the LDO regulator outputs. To place the device in PM2 or PM6, the core should execute a wait-for-interrupt (WFI) or wait-for-event (WFE) instruction. If the WFI instruction is called from an interrupt service routine, the interrupt that wakes the device from PM2 or PM6 must be of a sufficient priority to be recognized by the core. It is recommended to perform both a DSB (Data Synchronization Barrier) and an ISB (Instruction Syncronization Barrier) operation prior to the WFI to ensure all bus accesses complete. When operating from the LFOSC0, PM6 can achieve similar power consumption to PM3, but with faster wake times and the ability to wake on any interrupt.

4.1.5.4. Power Mode 3

In Power Mode 3 the core and peripheral clocks are halted. The available sources to wake from PM3 are controlled by the Power Management Unit (PMU). A special Fast Wake option allows the core to wake faster by keeping the LFOSC0 or RTC0 clock active. Because the current consumption of these blocks is minimal, it is recommended to use the fast wake option.

Before entering PM3, the DMA controller should be disabled, and the desired wake source(s) should be configured in the PMU. The SLEEPDEEP bit in the ARM System Control Register should be set, and the PMSEL bit in the CLKCTRL0_CONFIG register should be cleared to indicate that PM3 is the desired power mode. For fast wake, the core clocks (AHB and APB) should be configured to run from the LPOSC, and the PM3 Fast wake option and clock source should be selected in the PM3CN register.

The device will enter PM3 on a WFI or WFE instruction. If the WFI instruction is called from an interrupt service routine, the interrupt that wakes the device from PM3 must be of a sufficient priority to be recognized by the core. It is recommended to perform both a DSB (Data Synchronization Barrier) and an ISB (Instruction Synchronization Barrier) operation prior to the WFI to ensure all bus access is complete.

4.1.5.5. Power Mode 8

In Power Mode 8, the core and most peripherals are completely powered down, but all registers and selected RAM blocks retain their state. The LDO regulators are disabled, so all active circuitry operates directly from VBAT. Alternatively, the PMU has a specialized VBAT-divided-by-2 charge pump that can power some internal modules while in PM8 to save power. The fully operational functions in this mode are: LPTIMER0 , RTC0, UART0 running from RTC0TCLK, PMU Pin Wake, the advanced capture counter, and the LCD controller.

This mode provides the lowest power consumption for the device, but requires an appropriate wake up source or reset to exit. The available wake up or reset sources to wake from PM8 are controlled by the Power Management Unit (PMU). The available wake up sources are: Low Power Timer (LPTIMER0), RTC0 (alarms and oscillator failure notification), Comparator 0 (CMP0), advanced capture counter (ACCTR0), LCD VBAT monitor (LCD0), UART0, low power mode charge pump failure, and PMU Pin Wake. The available reset sources are: RESET pin, VBAT supply monitor, Comparator 0, Comparator 1, low power mode charge pump failure, RTC0 oscillator failure, or a PMU wake event.

Before entering PM8, the desired wake source(s) should be configured in the PMU. The SLEEPDEEP bit in the ARM System Control Register should be set, and the PMSEL bit in the CLKCTRL0_CONFIG register should be set to indicate that PM8 is the desired power mode.

The device will enter PM8 on a WFI or WFE instruction, and remain in PM8 until a reset configured by the PMU occurs. It is recommended to perform both a DSB (Data Synchronization Barrier) and an ISB (Instruction Synchronization Barrier) operation prior to the WFI to ensure all bus access is complete.

4.5. Data Peripherals

4.5.1. 10-Channel DMA Controller

The DMA facilitates autonomous peripheral operation, allowing the core to finish tasks more quickly without spending time polling or waiting for peripherals to interrupt. This helps reduce the overall power consumption of the system, as the device can spend more time in low-power modes.

The DMA controller has the following features:

- Utilizes ARM PrimeCell uDMA architecture.
- Implements 10 channels.
- DMA crossbar supports DTM0, DTM1, DTM2, SARADC0, IDAC0, I2C0, SPI0, SPI1, USART0, AES0, ENCDEC0, EPCA0, external pin triggers, and timers.
- Supports primary, alternate, and scatter-gather data structures to implement various types of transfers.
- Access allowed to all AHB and APB memory space.

4.5.2. Data Transfer Managers (DTM0, DTM1, DTM2)

The Data Transfer Manager is a module that collects DMA request signals from various peripherals and generates a series of master DMA requests based on a state-driven configuration. This master request drives a set of DMA channels to perform functions such as assembling and transferring communication packets to external devices. This capability saves power by allowing the core to remain in a low power mode during complex transfer operations. A combination of simple and peripheral scatter-gather DMA configurations can be used to perform complex operations while reducing memory requirements.

The DTM acts as a side channel for the peripheral's DMA control signals. When active, it manages the DMA control signals for the peripherals. When the DTMn module is inactive, the peripherals communicate directly to the DMA module.

The DTMn module has the following features:

- State descriptions stored in RAM with up to 15 states supported per module.
- Supports up to 15 source peripherals and up to 15 destination peripherals per module, in addition to memory or peripherals that do not require a data request.
- Includes error detection and an optional transfer timeout.
- Includes notifications for state transitions.

4.5.3. 128/192/256-bit Hardware AES Encryption (AES0)

The basic AES block cipher is implemented in hardware. The integrated hardware support for Cipher Block Chaining (CBC) and Counter (CTR) algorithms results in identical performance, memory bandwidth, and memory footprint between the most basic Electronic Codebook (ECB) algorithm and these more complex algorithms. This hardware accelerator translates to more core bandwidth available for other functions or a power savings for low-power applications.

The AES module includes the following features:

- Operates on 4-word (16-byte) blocks.
- Supports key sizes of 128, 192, and 256 bits for both encryption and decryption.
- Generates the round key for decryption operations.
- All cipher operations can be performed without any firmware intervention for multiple 4-word blocks (up to 32 kB).
- Support for various chained and stream-ciphering configurations with XOR paths on both the input and output.
- Internal 4-word FIFOs to facilitate DMA operations.
- Integrated key storage.
- Hardware acceleration for Electronic Codebook (ECB), Cipher-Block Chaining (CBC), and Counter (CTR) algorithms utilizing integrated counterblock generation and previous-block caching.

4.6.3. Real-Time Clock (RTC0)

The RTC module includes a 32-bit timer that allows up to 36 hours of independent time-keeping when used with a 32.768 kHz watch crystal. The RTC provides three alarm events in addition to a missing clock event, which can also function as interrupt, reset, or wakeup sources on SiM3L1xx devices.

The RTC module includes internal loading capacitors that are programmable to 16 discrete levels, allowing compatibility with a wide range of crystals.

The RTC timer clock can be buffered and routed to a port bank pin to provide an accurate, low frequency clock to other devices while the core is in its lowest power down mode. The module also includes a low power internal low frequency oscillator that reduces low power mode current and is available for other modules to use as a clock source.

The RTC module includes the following features:

- 32-bit timer (supports up to 36 hours) with three separate alarms.
- Option for one alarm to automatically reset the RTC timer.
- Missing clock detector.
- Can be used with the internal Low Frequency Oscillator or with an external 32.768 kHz crystal (no additional resistors or capacitors necessary).
- Programmable internal loading capacitors support a wide range of external 32.768 kHz crystals.
- The RTC timer clock (RTC0CLK) can be buffered and routed to an I/O pin to provide an accurate, low frequency clock to other devices while the core is in its lowest power down mode.
- The RTC module can be powered from the low power mode charge pump for lowest possible power consumption while in PM8.

4.6.4. Low Power Timer (LPTIMER0)

The Low Power Timer (LPTIMER) module runs from the RTC timer clock (RTC0CLK), allowing the LPTIMER to operate even if the AHB and APB clocks are disabled. The LPTIMER counter can increment using one of two clock sources: the clock selected by the RTC0 module, or rising or falling edges of an external signal.

The Low Power Timer includes the following features:

- Runs on low-frequency RTC timer clock (RTC0TCLK).
- The LPTIMER counter can increment using one of two clock sources: the RTC0TCLK or rising or falling edges of an external signal.
- Overflow and threshold-match detection.
- Timer reset on threshold-match allows square-wave generation at a variable output frequency.
- Supports PWM with configurable period and duty cycle.
- The LPTIMER module can be powered from the low power mode charge pump for lowest possible power consumption while in PM8.

4.6.5. Watchdog Timer (WDTIMER0)

The WDTIMER module includes a 16-bit timer, a programmable early warning interrupt, and a programmable reset period. The timer registers are protected from inadvertent access by an independent lock and key interface.

The watchdog timer runs from the low frequency oscillator (LFOSC0).

The Watchdog Timer has the following features:

- Programmable timeout interval.
- Optional interrupt to warn when the Watchdog Timer is nearing the reset trip value.
- Lock-out feature to prevent any modification until a system reset.

Table 6.1. Pin Definitions and Alternate Functions for SiM3L1x7

Pin Name	Type	Pin Numbers (TQFP-80)	I/O Voltage Domain	Crossbar Capability	Port Match	LCD Interface	Output Toggle Logic	External Trigger Inputs / Digital Functions	Analog Functions
VSS	Ground	12 31 52 71							
VSSDC	Ground (DC-DC)	12							
VIO	Power (I/O)	7 30 68							
VIORF	Power (RF I/O)	8							
VBAT/ VBATDC		10							
VDRV		9							
VDC		13							
VLCD	Power (LCD Charge Pump)	67							
IND	DC-DC Inductor	11							
$\overline{\text{RESET}}$	Active-low Reset	72							
TCK/ SWCLK	JTAG / Serial Wire	6							
TMS/ SWDIO	JTAG / Serial Wire	5							
RTC1	RTC Oscillator Input	70							
RTC2	RTC Oscillator Output	69							

Table 6.1. Pin Definitions and Alternate Functions for SiM3L1x7 (Continued)

Pin Name	Type	Pin Numbers (TQFP-80)	I/O Voltage Domain	Crossbar Capability	Port Match	LCD Interface	Output Toggle Logic	External Trigger Inputs / Digital Functions	Analog Functions
PB1.8	Standard I/O	58	VIO	✓	✓	LCD0.31			CMP0P.3
PB1.9	Standard I/O	57	VIO	✓	✓	LCD0.30			CMP0N.3
PB1.10	Standard I/O	56	VIO	✓	✓	LCD0.29			CMP1P.3
PB1.11	Standard I/O	55	VIO	✓	✓	LCD0.28			CMP1N.3
PB2.0	Standard I/O	54	VIORF	✓	✓			LPT0T8 INT1.0 WAKE.12 SPI1_CTS	ADC0.8 CMP0P.4
PB2.1	Standard I/O	53	VIORF	✓	✓			LPT0T9 INT1.1 WAKE.13 VIORFCLK	ADC0.9 CMP0N.4
PB2.4	Standard I/O	51	VIORF	✓	✓			LPT0T12 INT1.4 SPI1_SCLK	ADC0.10 CMP0P.5
PB2.5	Standard I/O	50	VIORF	✓	✓			LPT0T13 INT1.5 SPI1_MISO	ADC0.11 CMP0N.5
PB2.6	Standard I/O	49	VIORF	✓	✓			LPT0T14 INT1.6 SPI1_MOSI	ADC0.12 CMP1P.5
PB2.7	Standard I/O	48	VIORF	✓	✓			INT1.7 SPI1_NSS	ADC0.13 CMP1N.5
PB3.0	Standard I/O	47	VIO	✓	✓	LCD0.27		INT1.8	ADC0.14
PB3.1	Standard I/O	46	VIO	✓	✓	LCD0.26		INT1.9	ADC0.15
PB3.2	Standard I/O	45	VIO	✓	✓	LCD0.25		INT1.10	ADC0.16
PB3.3	Standard I/O	44	VIO	✓	✓	LCD0.24		INT1.11	ADC0.17

Table 6.3. Pin Definitions and Alternate Functions for SiM3L1x4

Pin Name	Type	Pin Numbers	I/O Voltage Domain	Crossbar Capability	Port Match	Output Toggle Logic	External Trigger Inputs / Digital Functions	Analog Functions
VSS	Ground	9 25						
VSSDC	Ground (DC-DC)	9						
VIO	Power (I/O)	5						
VIORF / VDRV	Power (RF I/O)	6						
VBAT / VBATDC		7						
VDC		10						
IND	DC-DC Inductor	8						
$\overline{\text{RESET}}$	Active-low Reset	35						
SWCLK	Serial Wire	4						
SWDIO	Serial Wire	3						
RTC1	RTC Oscillator Input	34						
RTC2	RTC Oscillator Output	33						
PB0.0	Standard I/O	2	VIO	XBR0	✓	✓	INT0.0 WAKE.0	ADC0.20 VREF CMP0P.0
PB0.1	Standard I/O	1	VIO	XBR0	✓	✓	INT0.1 WAKE.2	ADC0.22 CMP0N.0 CMP1P.0 XTAL2

Table 6.4. TQFP-80 Package Dimensions

Dimension	Min	Nominal	Max
A	—	—	1.20
A1	0.05	—	0.15
A2	0.95	1.00	1.05
b	0.17	0.20	0.27
c	0.09	—	0.20
D	14.00 BSC		
D1	12.00 BSC		
e	0.50 BSC		
E	14.00 BSC		
E1	12.00 BSC		
L	0.45	0.60	0.75
L1	1.00 Ref		
Θ	0°	3.5°	7°
aaa	0.20		
bbb	0.20		
ccc	0.08		
ddd	0.08		
eee	0.05		

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This package outline conforms to JEDEC MS-026, variant ADD.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

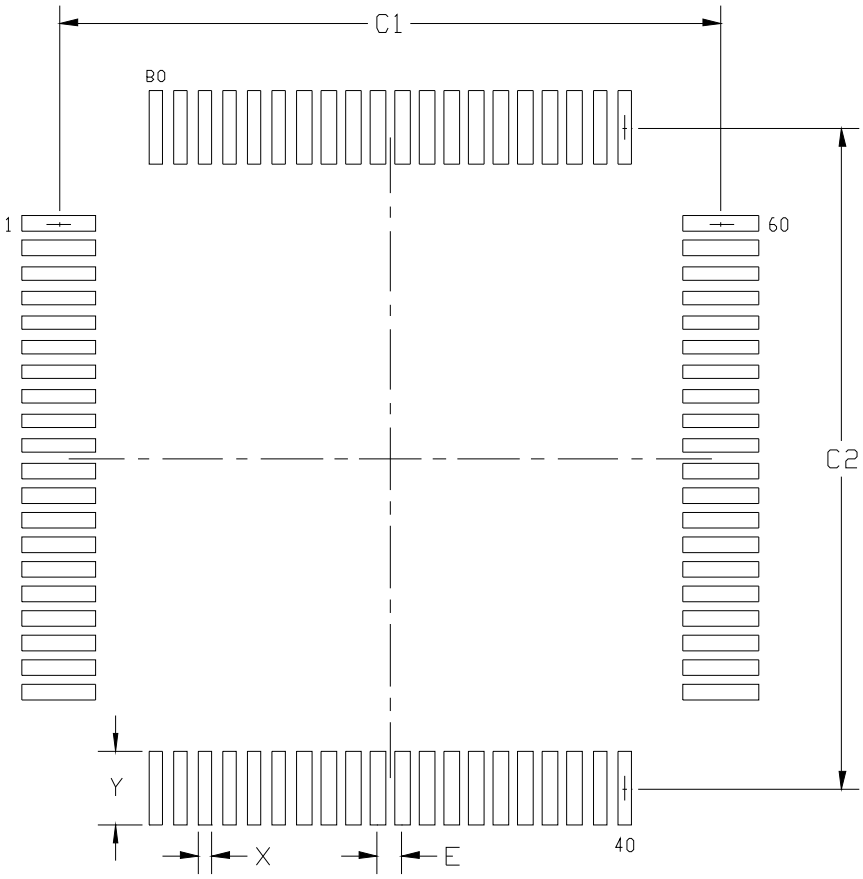

Figure 6.6. TQFP-80 Landing Diagram

Table 6.5. TQFP-80 Landing Diagram Dimensions

Dimension	Min	Max
C1	13.30	13.40
C2	13.30	13.40
E	0.50 BSC	
X	0.20	0.30
Y	1.40	1.50

Notes:
1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This land pattern design is based on the IPC-7351 guidelines.

6.6. TQFP-64 Package Specifications

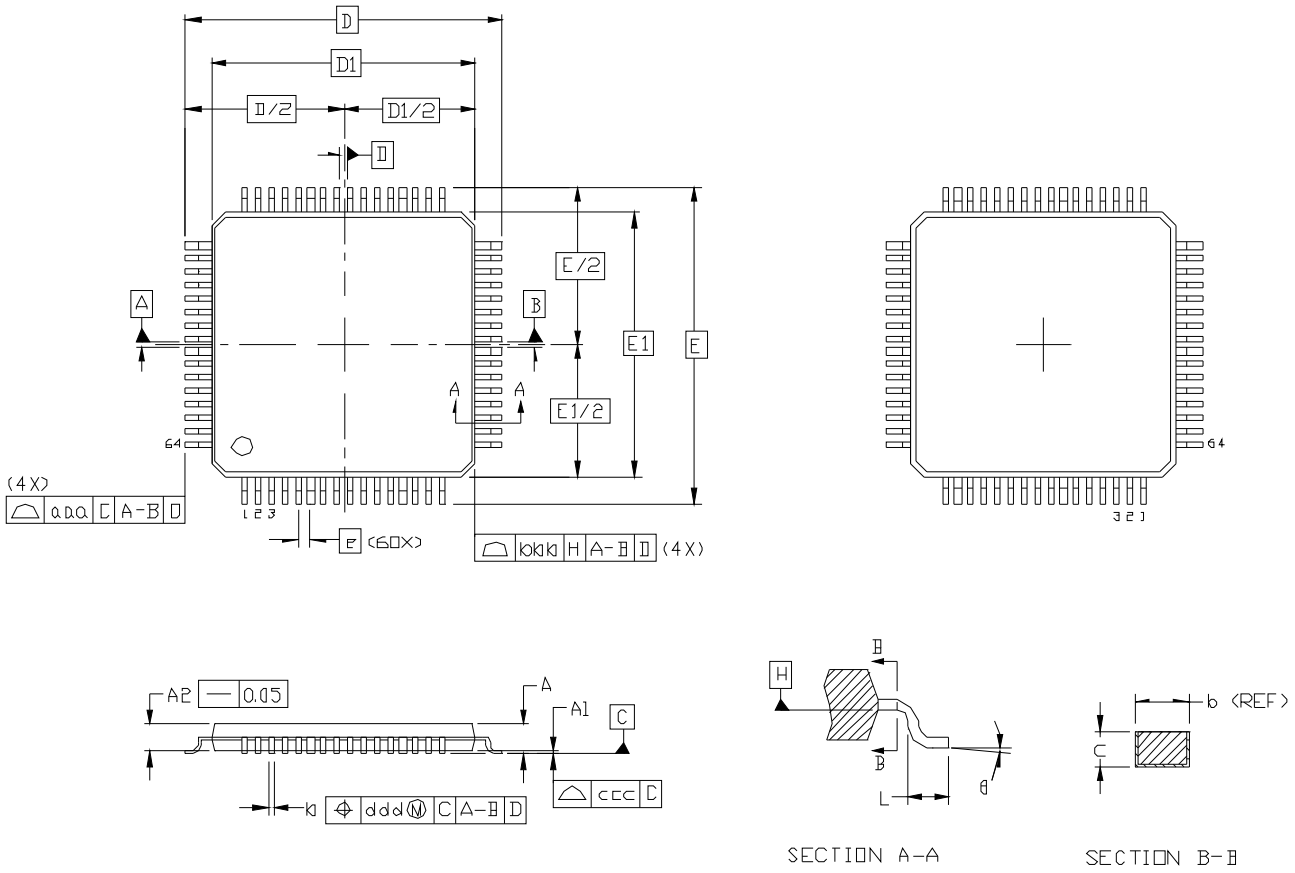

Figure 6.9. TQFP-64 Package Drawing

Table 6.8. TQFP-64 Package Dimensions

Dimension	Min	Nominal	Max
A	—	—	1.20
A1	0.05	—	0.15
A2	0.95	1.00	1.05
b	0.17	0.22	0.27
c	0.09	—	0.20
D	12.00 BSC		
D1	10.00 BSC		
e	0.50 BSC		
E	12.00 BSC		
E1	10.00 BSC		
L	0.45	0.60	0.75
Θ	0°	3.5°	7°
aaa	—	—	0.20
bbb	—	—	0.20
ccc	—	—	0.08
ddd	—	—	0.08

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This package outline conforms to JEDEC MS-026, variant ACD.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

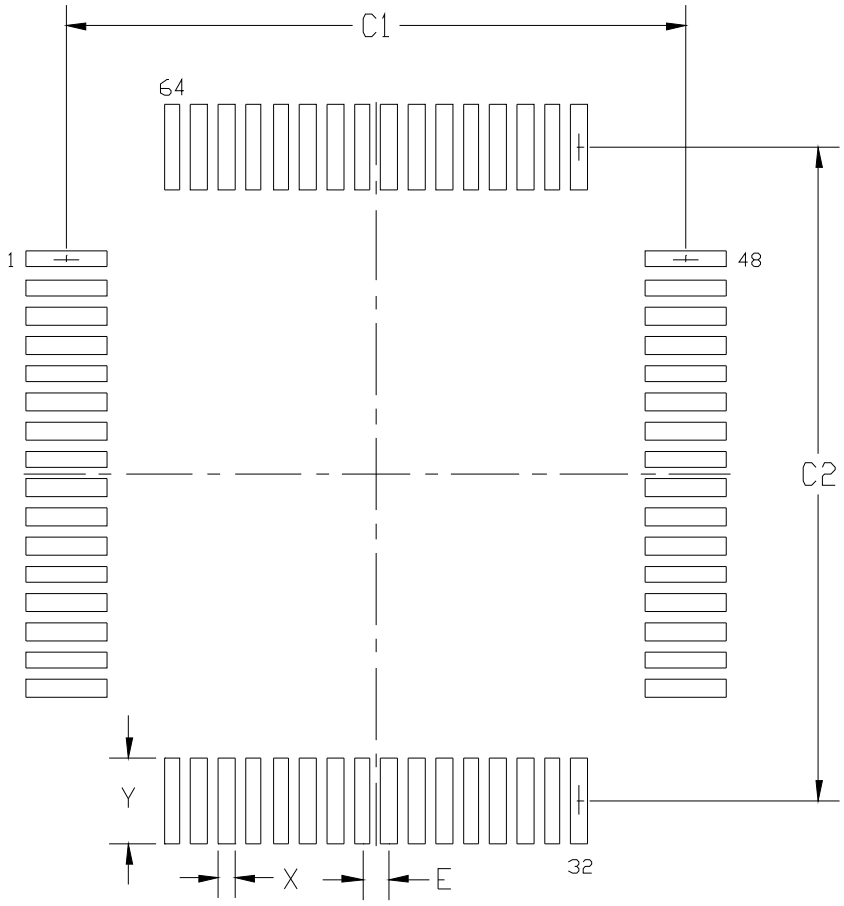

Figure 6.10. TQFP-64 Landing Diagram

Table 6.9. TQFP-64 Landing Diagram Dimensions

Dimension	Min	Max
C1	11.30	11.40
C2	11.30	11.40
E	0.50 BSC	
X	0.20	0.30
Y	1.40	1.50

Notes:
1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This land pattern design is based on the IPC-7351 guidelines.